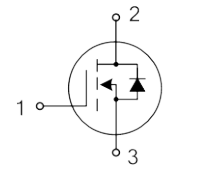
18A, 600V N-CHANNEL MOSFET

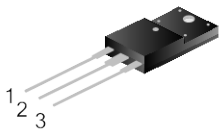
GENERAL DESCRIPTION

SVF18N60F is an N-channel enhancement mode power MOS field effect transistor which is produced using Silan proprietary F-Cell™ structure VDMOS technology. The improved planar stripe cell and the improved guarding ring terminal have been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are widely used in AC-DC power suppliers, DC-DC converters and H-bridge PWM motor drivers.



1.Gate 2.Drain 3.Source



TO-220F-3L

FEATURES

- 18A,600V,$R_{DS(on)}$ (typ) =0.36Ω@V_{GS}=10V
- Low gate charge
- Low Crss
- Fast switching
- Improved dv/dt capability

NOMENCLATURE

S V F X N E X X X

Silan VDMOS Code of F-Cell process

Nominal current,using 1 or 2 digits:
Example:4 denotes 4A,
10 denotes 10A,
08 denotes 0.8A

N denotes N Channel

Special Features indication, May be omitted.
Example: E denotes embeded ESD structure

Nominal Voltage,using 2 digits
Example: 60 denotes 600V,
65 denotes 650V.

Package information.
Example:F:TO-220F.

ORDERING INFORMATION

Part No.	Package	Marking	Material	Packing
SVF18N60F	TO-220F-3L	SVF18N60F	Pb free	Tube

ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Characteristics		Symbol	Ratings	Unit
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	±30	V
Drain Current	T_C=25°C	I_D	18	A
	T_C=100°C		11.4	
Drain Current Pulsed		I_{DM}	72	A
Power Dissipation(T_C=25°C)		P_D	54	W
-Derate above 25°C			0.43	W/°C
Single Pulsed Avalanche Energy (Note 1)		E_{AS}	1185	mJ
Operation Junction Temperature Range		T_J	-55～+150	°C
Storage Temperature Range		T_{stg}	-55～+150	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Ratings	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.31	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	120	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain -Source Breakdown Voltage	B_{VDSS}	V_{GS}=0V, I_D=250μA	600	--	--	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=600V, V_{GS}=0V	--	--	1.0	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±30V, V_{DS}=0V	--	--	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}= V_{DS}, I_D=250μA	2.0	--	4.0	V
Static Drain- Source On State Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=9.0A	--	0.36	0.45	Ω
Input Capacitance	C_{iss}	V_{DS}=25V, V_{GS}=0V, f=1.0MHZ	--	2347.40	3051.62	pF
Output Capacitance	C_{oss}		--	250.20	325.26	
Reverse Transfer Capacitance	C_{rss}		--	5.50	9.60	
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=300V, R_G=25Ω, I_D=18A (Note 2,3)	--	26.04	33.85	ns
Turn-on Rise Time	t_r		--	40.16	52.21	
Turn-off Delay Time	$t_{d(off)}$		--	61.12	79.46	
Turn-off Fall Time	t_f		--	35.28	45.86	
Total Gate Charge	Q_g	V_{DS}=480V, I_D=18A, V_{GS}=10V (Note 2,3)	--	40.05	52.07	nC
Gate-Source Charge	Q_{gs}		--	12.91	16.78	
Gate-Drain Charge	Q_{gd}		--	12.21	15.87	
Gate resistance	R_G	F=1MHz, Gate DC Bias=0, Test signal level=20mV, open drain	--	5.40	7.28	Ω

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	Integral Reverse P-N Junction Diode in the MOSFET	--	--	18	A
Pulsed Source Current	I_{SM}		--	--	72	
Diode Forward Voltage	V_{SD}	I_S=18A,V_{GS}=0V	--	--	1.4	V
Reverse Recovery Time	T_{rr}	I_S=18A,V_{GS}=0V, dI_F/dt=100A/μS	--	642.87	835.73	ns
Reverse Recovery Charge	Q_{rr}		--	8.01	11.20	μC

Notes:

1. L=30mH, I_{AS}=8.25, V_{GS}=50V, R_G=25Ω, starting T_J=25°C;
2. Pulse Test: Pulse width ≤300μs,Duty cycle≤2%;
3. Essentially independent of operating temperature.

TYPICAL CHARACTERISTICS

Figure 1. On-Region Characteristics

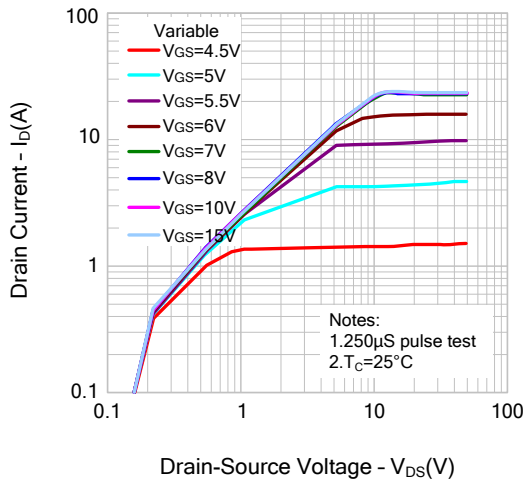


Figure 2. Transfer Characteristics

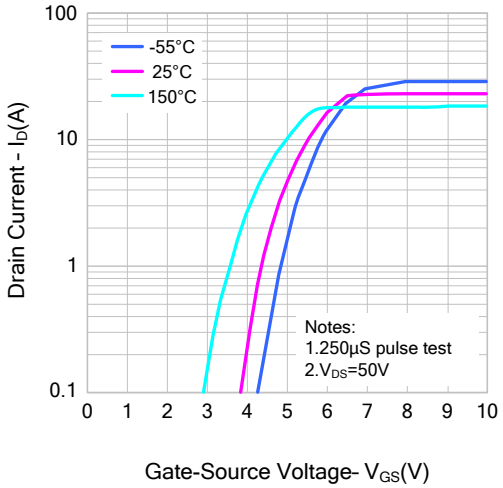


Figure 3. On-Resitance Variation vs. Drain Current and Gate Voltage

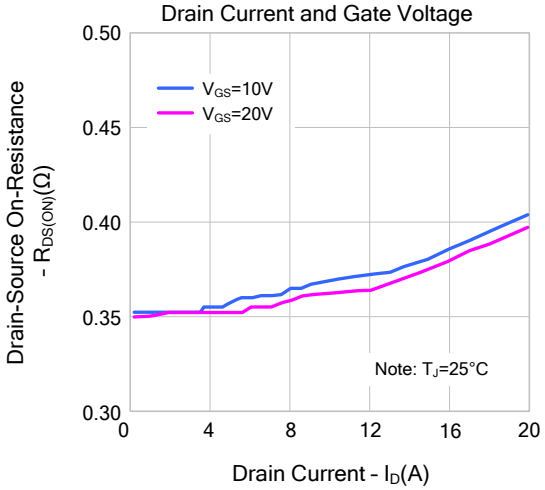
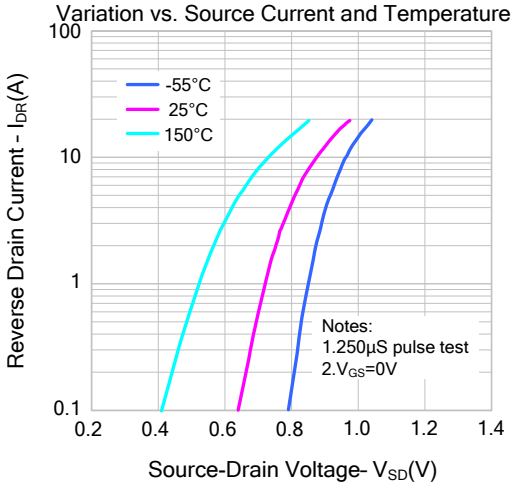


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature



TYPICAL CHARACTERISTICS (continued)

Figure 5. Capacitance Characteristics

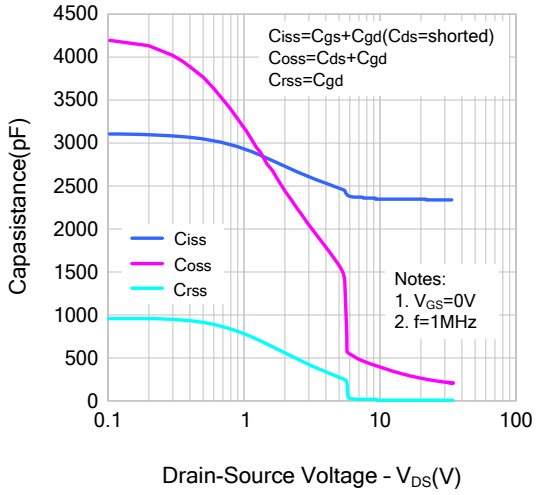


Figure 6. Gate Charge Characteristics

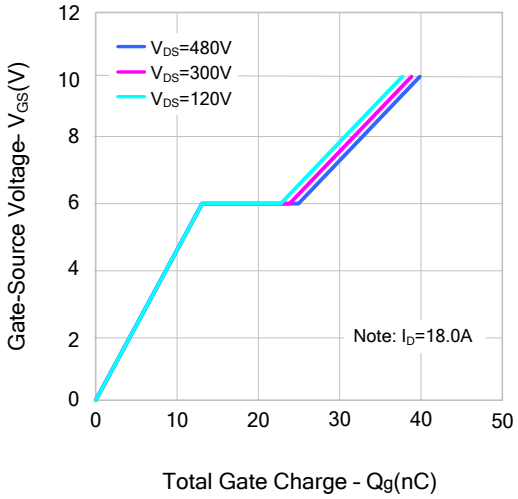


Figure 7. Breakdown Voltage Variation vs. Temperature

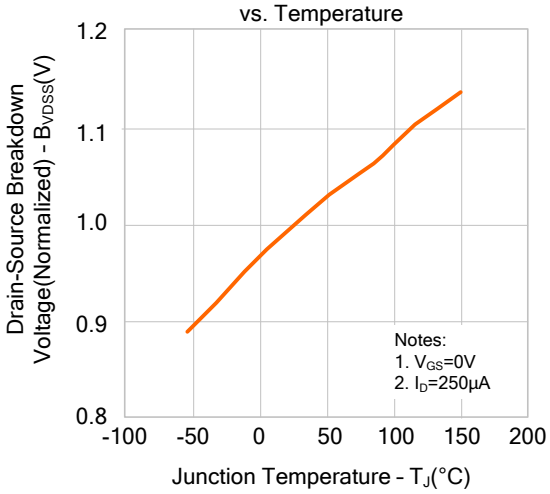


Figure 8. On-resistance Variation vs. Temperature

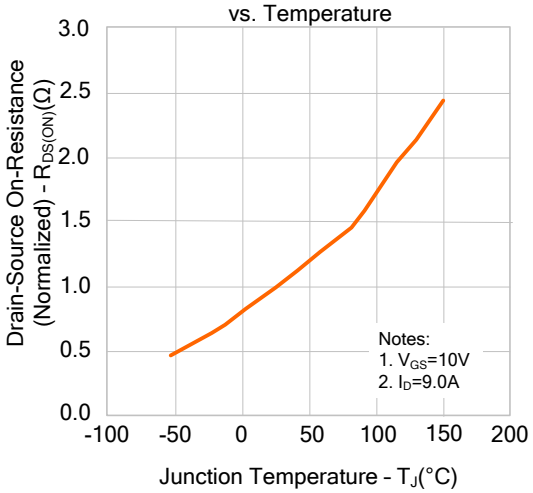


Figure 9. Max. Safe Operating Area

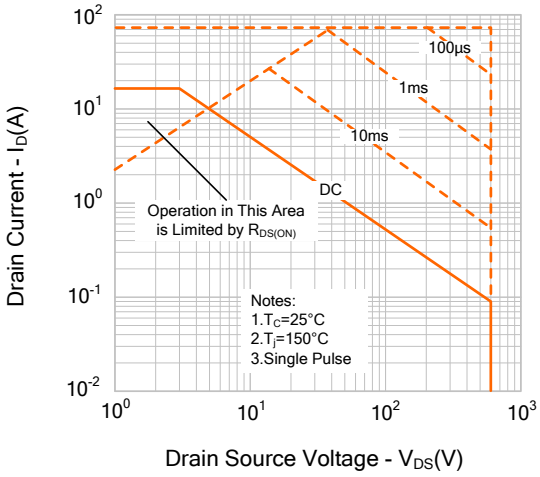
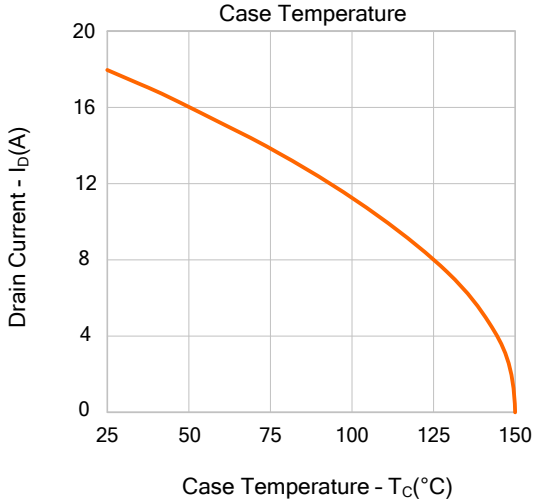
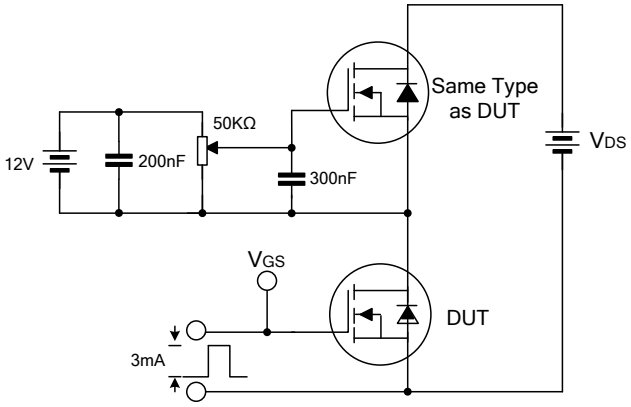


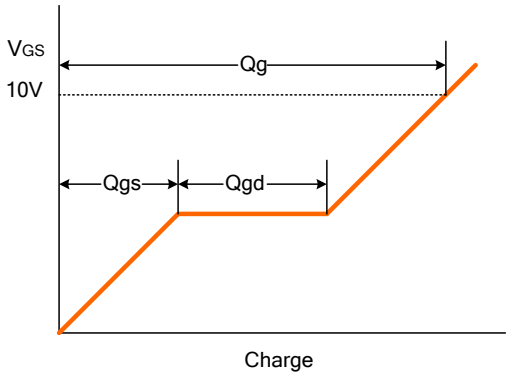
Figure 10. Maximum Drain Current vs. Case Temperature



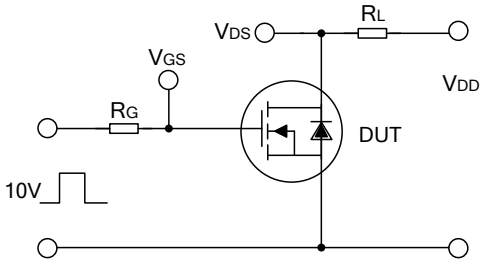
TYPICAL TEST CIRCUIT

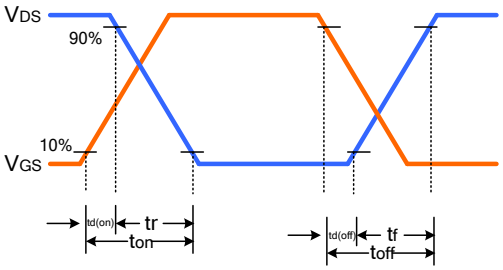
Gate Charge Test Circuit & Waveform



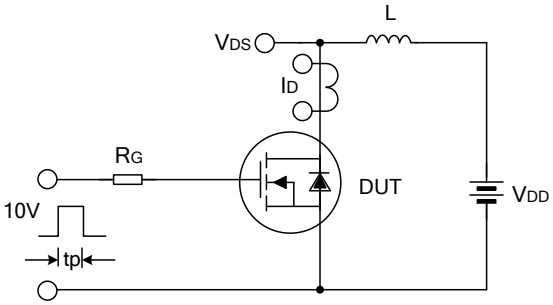


Resistive Switching Test Circuit & Waveform

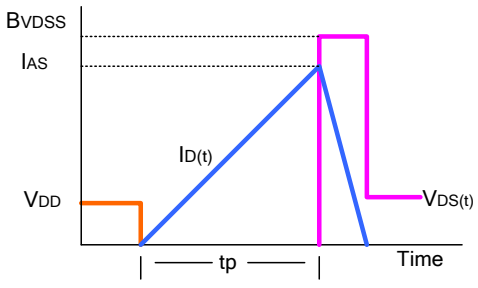




Unclamped Inductive Switching Test Circuit & Waveform

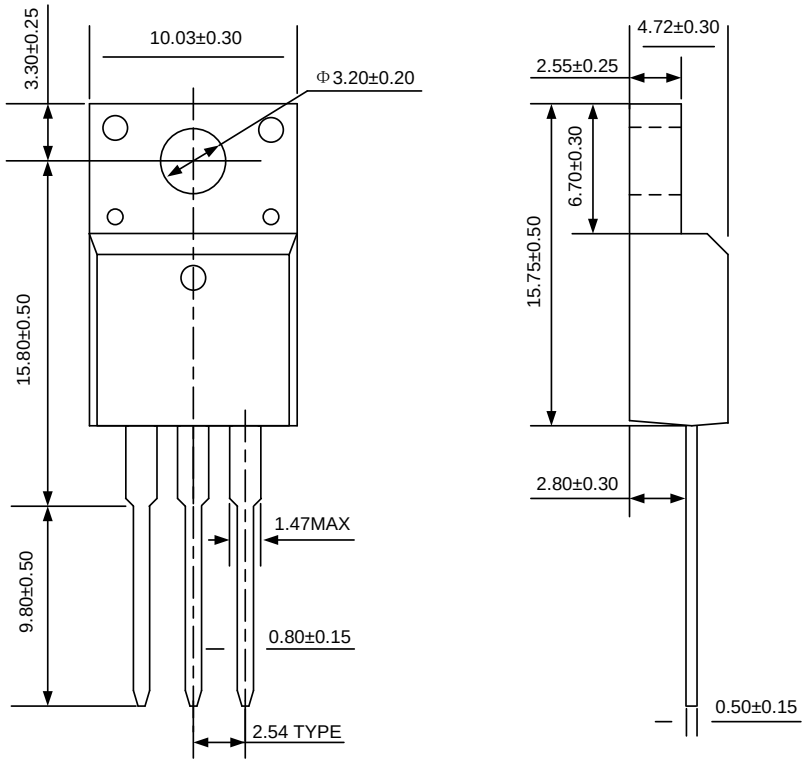


$$E_{AS} = \frac{1}{2} LI_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



PACKAGE OUTLINE

TO-220F-3L UNIT: mm



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- **Silan will supply the best possible product for customers!**

ATTACHMENT

Revision History

Date	REV	Description	Page
2012.07.30	1.0	Initial release	